

**FIELD EFFECT TRANSISTOR AND METHOD OF ITS
MANUFACTURE**

ABSTRACT OF THE DISCLOSURE

5 A trenched field effect transistor is provided that includes (a) a semiconductor
substrate, (b) a trench extending a predetermined depth into the semiconductor substrate, (c) a
pair of doped source junctions, positioned on opposite sides of the trench, (d) a doped heavy
body positioned adjacent each source junction on the opposite side of the source junction
from the trench, the deepest portion of the heavy body extending less deeply into said
semiconductor substrate than the predetermined depth of the trench, and (e) a doped well
10 surrounding the heavy body beneath the heavy body.

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